

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 20 A, 650 V, D1, T0-247-2L

FFSH2065A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

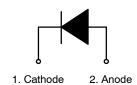
- Max Junction Temperature 175°C
- Avalanche Rated 95 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

Applications

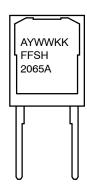
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



V _{RRM}	l _F	
650 V	20 A	



MARKING DIAGRAM



A = Assembly Plant Code
YWW = Date Code (Year & Week)
KK = Lot Traceability Code
FFSH2065A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH2065A	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)	Single Pulse Avalanche Energy (Note 1)		mJ
I _F	Continuous Rectified Forward Current @ Tc < 146°C		20	Α
		@ Tc < 135°C	25	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	on-Repetitive Peak Forward Surge Current		Α
		Tc = 150°C, 10 μs	1000	Α
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	105	Α
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	58	Α
P _{tot}	Power Dissipation	Tc = 25°C	183	W
		Tc = 150°C	31	W
T _J , T _{STG}	Operating and Storage Temperature Range TO247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 95 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 19.5$ A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol Parameter		Rating	Unit
R _{0JC} Thermal Resistance, Junction to Case, Max.		0.82	°C/W

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_C = 25^{\circ}C \ unless \ otherwise \ noted)$

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _F	Forward Voltage	IF = 20 A, Tc = 25°C	-	1.50	1.75	V
		IF = 20 A, Tc = 125°C	-	1.6	2.0	
		IF = 20 A, Tc = 175°C	-	1.72	2.4	
I _R	Reverse Current	VR = 650 V, Tc = 25°C	-	-	200	μΑ
		VR = 650 V, Tc = 125°C	-	-	400	
		V _R = 650 V, T _C = 175°C	-	-	600	
Q _C	Total Capacitive Charge	V = 400 V	-	64	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1085	-	pF
		VR = 200 V, f = 100 kHz	-	117	-	
		V _R = 400 V, f = 100 kHz	-	88	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH2065A	FFSH2065A	TO-247-2LD	Tube	N/A	N/A	30 Units

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

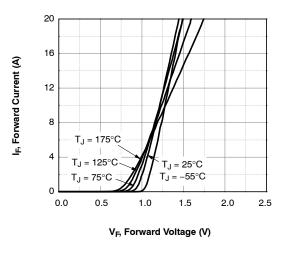
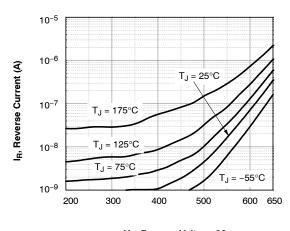


Figure 1. Forward Characteristics



V_R, Reverse Voltage (V)

Figure 2. Reverse Characteristics

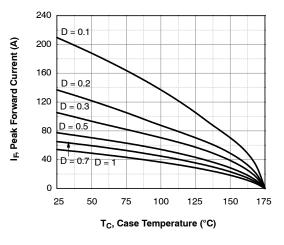


Figure 3. Current Derating

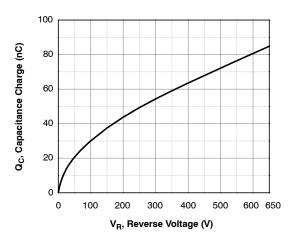


Figure 5. Capacitive Charge vs. Reverse Voltage

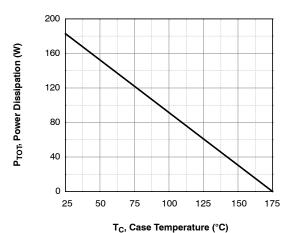


Figure 4. Power Derating

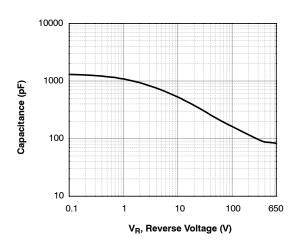


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS (CONTINUED)

(T_J = 25°C UNLESS OTHERWISE NOTED)

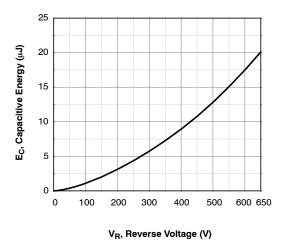


Figure 7. Capacitance Stored Energy

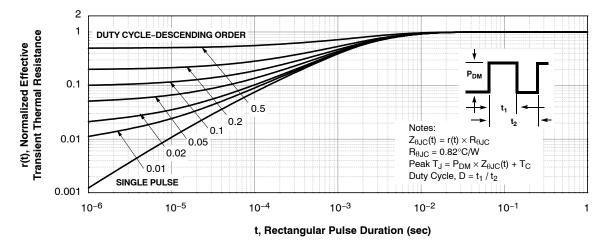
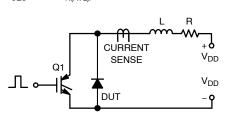


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$$\label{eq:local_local_local} \begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \ \Omega \\ V_{DD} &= 50 \ V \\ EAVL &= 1/2 LI2 \left[V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right] \\ Q1 &= IGBT \left(BV_{CES} > DUT \ V_{R(AVL)} \right) \end{split}$$



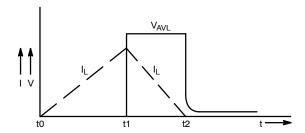
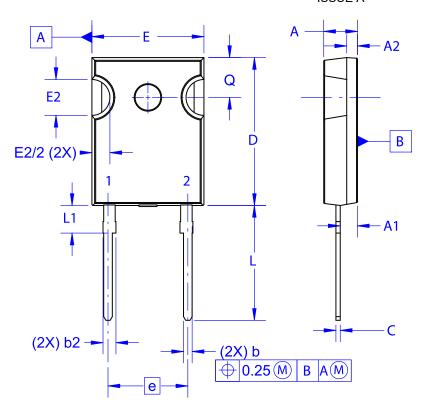


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

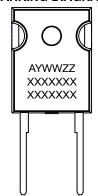
TO-247-2LD CASE 340CL **ISSUE A**





- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
 D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

= Assembly Location

= Year

WW = Work Week

= Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

	DATE 03 E	
Ø P —		Ø P1 D2
E1 —	1	D1
,		9

DIM	MILLIMETERS			
	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A1	2.29	2.40	2.66	
A2	1.30	1.50	1.70	
b	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	16.37	16.57	16.77	
D2	0.51	0.93	1.35	
Е	15.37	15.62	15.87	
E1	12.81	~	~	
E2	4.96	5.08	5.20	
е	~	11.12	~	
L	15.75	16.00	16.25	
L1	3.69	3.81	3.93	
ØΡ	3.51	3.58	3.65	
Ø P 1	6.61	6.73	6.85	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

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